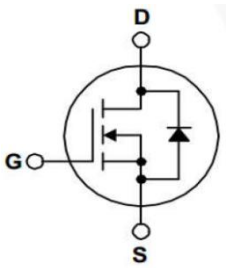
迈诺斯科技

IRF730

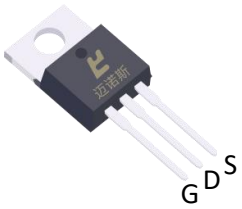
Silicon N-Channel Power MOSFET

Description

IRF730, the silicon N-channel Enhanced MOSFETs, is obtained by advanced MOSFET technology which reduce the conduction loss, improve switching performance and enhance the avalanche energy. The transistor is suitable device for SMPS, high speed switching and general purpose applications.



Schematic diagram



TO-220

General Features

① V_{DS}=500V,I_D=5A $R_{DS(ON)}$≦1.57Ω@V_{GS}=10V(Typ:1.31Ω)
② Fast Switching
③ Low Crss
④ 100% avalanche tested
⑤ Improved dv/dt capability
⑥ RoHS product

Application

① High frequency switching mode power supply

Package Marking And Ordering Information：

Ordering Codes	Package	Product Code	Packing
IRF730	TO-220	IRF730	Tube

Absolute Maximum Ratings (Tc=25℃ unless otherwise specified)

Symbol	Parameter	Value	Units
V_{DSS}	Drain-to-Source Voltage	500	V
I_D	Continuous Drain Current	5	A
	Continuous Drain Current T_C = 100°C	3.5	A
I_{DM}	Pulsed Drain Current(Note1)	20	A
V_{GS}	Gate-to-Source Voltage	±30	V
E_{AS}	Single Pulse Avalanche Energy(Note2)	350	mJ
dv/dt	Peak Diode Recovery dv/dt(Note3)	5.0	V/ns
P_D	Power Dissipation TO-220	78	W
	Derating Factor above 25°C	0.63	W/℃
T_J， T_{stg}	Operating Junction and Storage Temperature Range	150，–55 to 150	℃
T_L	Maximum Temperature for Soldering	300	℃

Thermal characteristics

Thermal characteristics (No FullPAK) TO-220

Symbol	Parameter	Value	Units
$R_{\theta JC}$	Junction-to-Case	1.6	℃/W
$R_{\theta JA}$	Junction-to-Ambient	62.5	℃/W

Electrical Parameters(at T_C = 25°C, unless otherwise specified)

OFF Characteristics

Symbol	Parameter	Test Conditions	Values			Units
			Min.	Typ.	Max.	
V_{DSS}	Drain to Source Breakdown Voltage	V_{GS}=0V, I_D=250μA	500	--	--	V
$\Delta B_{VDSS}/\Delta T_J$	Bvdss Temperature Coefficient	I_D=250uA, Reference25℃	--	0.58	--	V/℃
I_{DSS}	Drain to Source Leakage Current	V_{DS} =500V, V_{GS}= 0V,Tj = 25℃	--	--	1	μA
		V_{DS} =400V, V_{GS}= 0V,Tj=125℃	--	--	100	μA
$I_{GSS(F)}$	Gate to Source Forward Leakage	V_{GS} =+30V	--	--	100	nA
$I_{GSS(R)}$	Gate to Source Reverse Leakage	V_{GS} =-30V	--	--	100	nA

ON Characteristics

Symbol	Parameter	Test Conditions	Values			Units
			Min.	Typ.	Max.	
$R_{DS(ON)}$	Drain-to-Source On- Resistance	V_{GS}=10V, I_D=2.5A(Note4)	--	1.31	1.57	Ω
$V_{GS(TH)}$	Gate Threshold Voltage	V_{DS} = V_{GS}, I_D = 250μA(Note4)	2.0	3.0	4.0	V
g_{fs}	Forward Transconductance	V_{DS}=15V, I_D =5A(Note4)	--	3.5	--	S

Dynamic Characteristics

Symbol	Parameter	Test Conditions	Values			Units
			Min.	Typ.	Max.	
R_g	Gate resistance	f = 1.0MHz	--	3.0	--	Ω
C_{iss}	Input Capacitance	V_{GS} = 0V V_{DS} =25V f = 1.0MHz	--	690	--	PF
C_{oss}	Output Capacitance		--	65	--	
C_{rss}	Reverse Transfer Capacitance		--	2.45	--	

Switching Characteristics						
Symbol	**Parameter**	**Test Conditions**	**Values**			**Units**
			Min.	**Typ.**	**Max.**	
$t_{d(ON)}$	Turn-on Delay Time	I_D =5A V_{DD} = 250V V_{GS} = 10V R_G =5Ω	--	13	--	ns
t_r	Rise Time		--	45	--	
$t_{d(OFF)}$	Turn-Off Delay Time		--	50	--	
t_f	Fall Time		--	49	--	
Q_g	Total Gate Charge	I_D =5A V_{DD} =400V V_{GS} = 10V	--	16.8	--	nC
Q_{gs}	Gate to Source Charge		--	5.5	--	
Q_{gd}	Gate to Drain (“Miller”)Charge		--	4.3	--	

Source-Drain Diode Characteristics						
Symbol	**Parameter**	**Test Conditions**	**Values**			**Units**
			Min.	**Typ.**	**Max.**	
I_S	Continuous Source Current (Body Diode)	T_C=25 °C	--	--	5	A
I_{SM}	Maximum Pulsed Current (Body Diode)		--	--	20	A
V_{SD}	Diode Forward Voltage	I_S=5A, V_{GS}=0V(Note4)	--	--	1.2	V
T_{rr}	Reverse Recovery Time	I_S=5A, T_j = 25°C $d_{IF/dt}$=100A/us, V_{GS}=0V	--	264	--	ns
Q_{rr}	Reverse Recovery Charge		--	1950	--	nC

Note1: Pulse width limited by maximum junction temperature

Note2: L=10mH, V_{DS}=150V, Start T_J=25℃

Note3: I_{SD} =5A,di/dt ≤100A/us,V_{DD}≤B_{VDS}, Start T_J=25℃

Note4: Pulse width tp≤300μs, δ≤2%

Characteristics Curves

Figure 1a Safe Operating Area (No FullPAK)

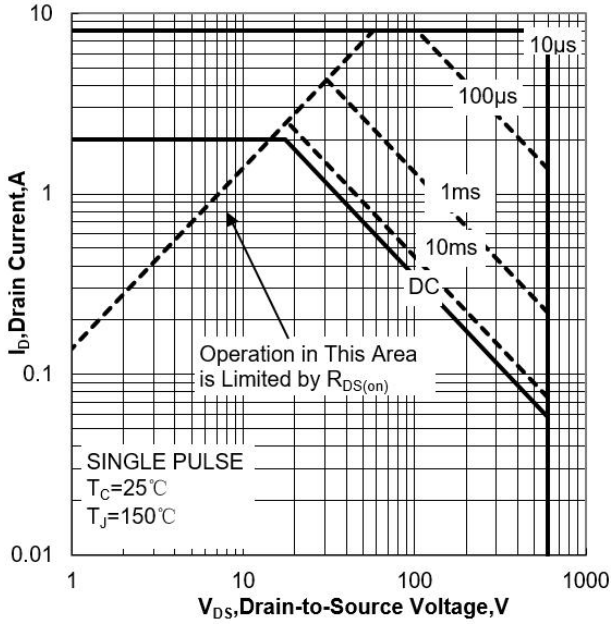


Figure 1b Safe Operating Area (FullPAK)

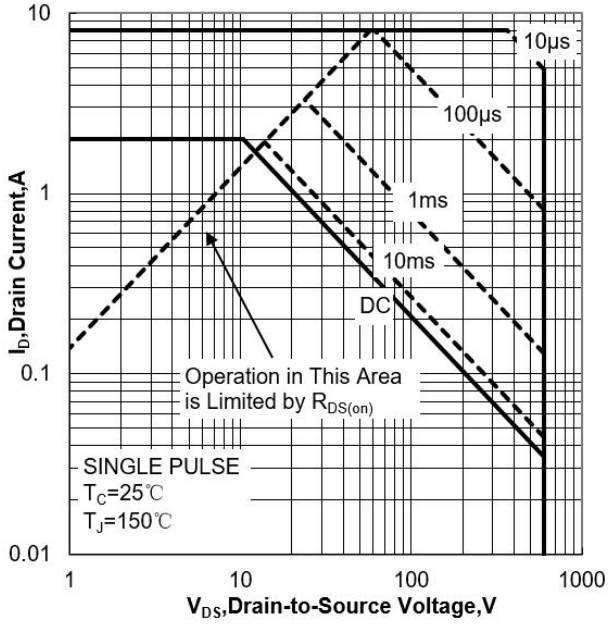


Figure 2a Power Dissipation (No FullPAK)

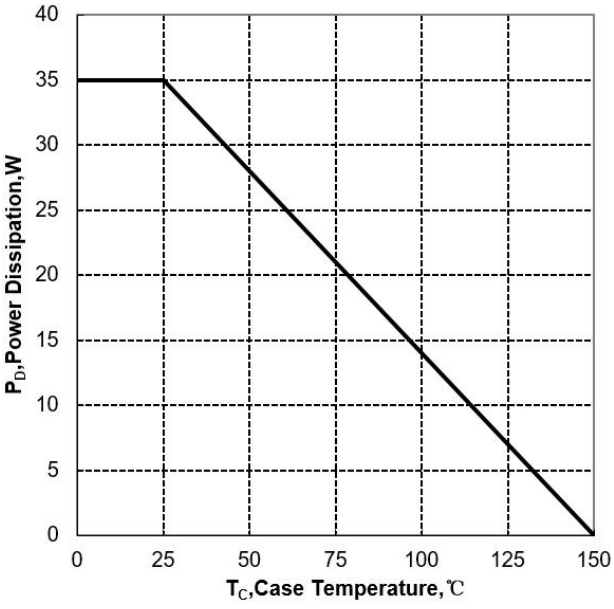


Figure 2b Power Dissipation (FullPAK)

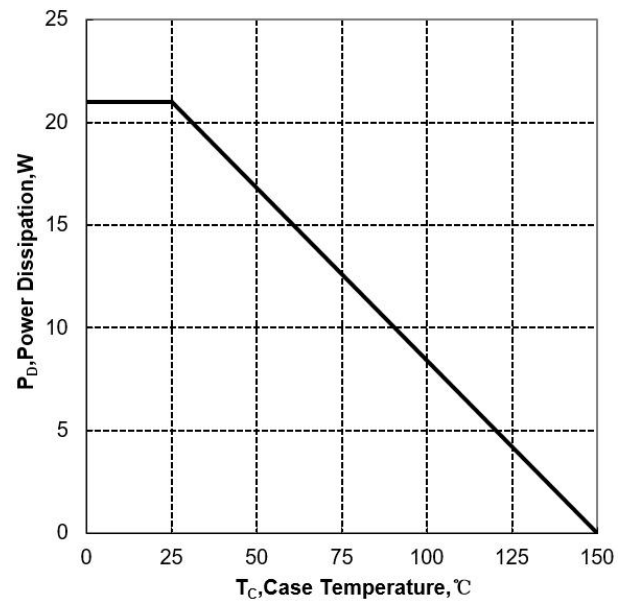


Figure 3a Max Thermal Impendance (No FullPAK)

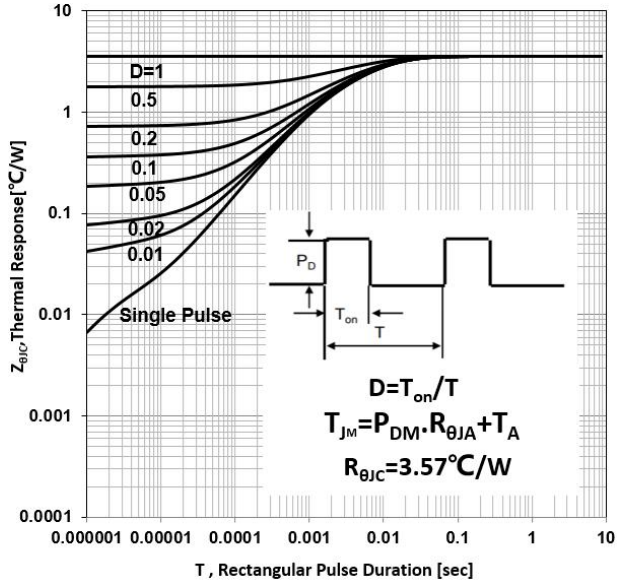


Figure 3b Max Thermal Impendance (FullPAK)

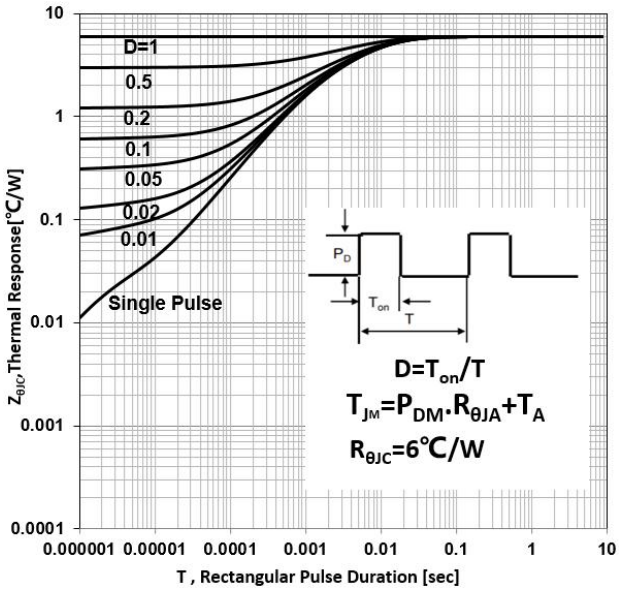


Figure 4 Typical Output Characteristics

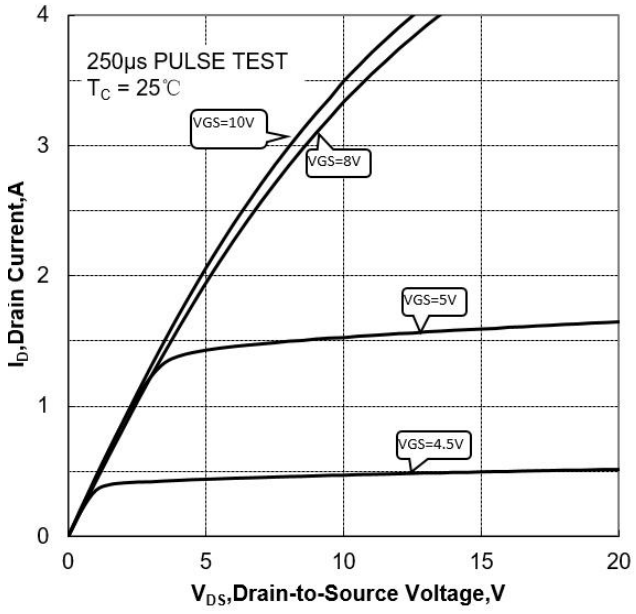


Figure 5 Typical Transfer Characteristics

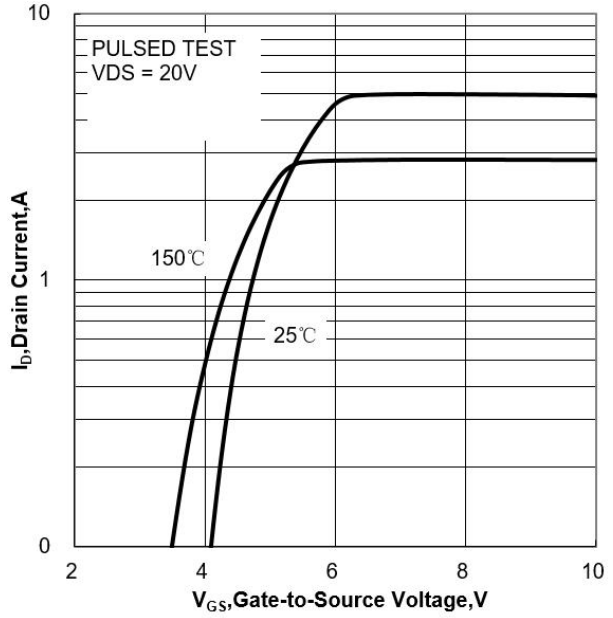


Figure 6 Typical Drain to Source ON Resistance vs Drain Current

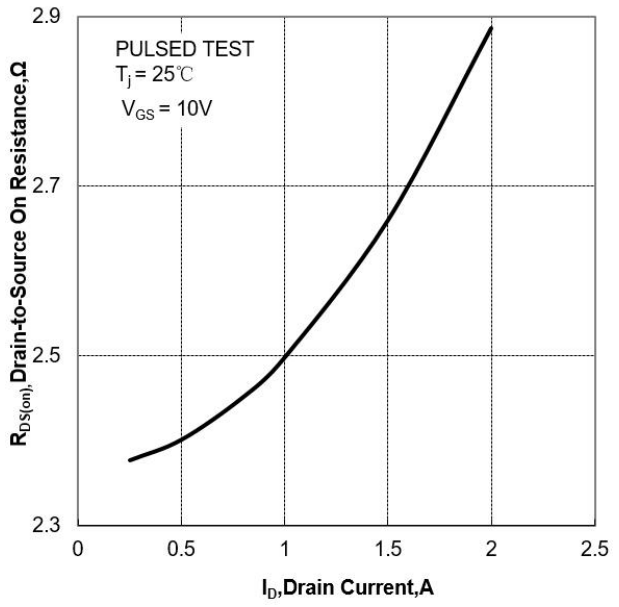


Figure 7 Typical Drian to Source on Resistance vs Junction Temperature

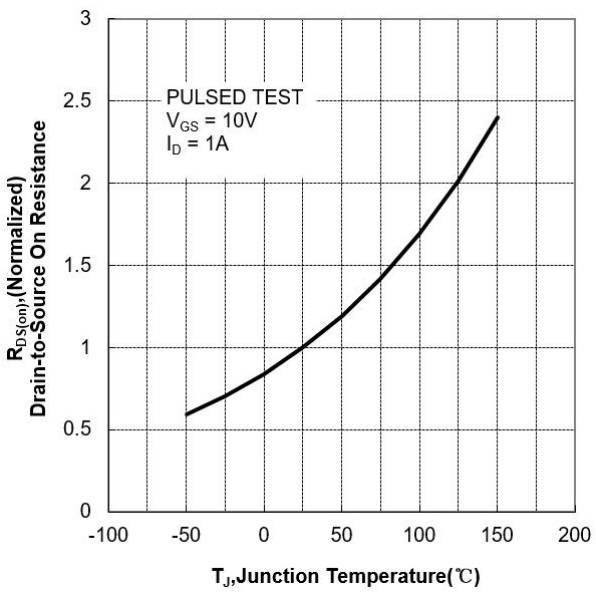


Figure 8 Typical Theshold Voltage vs Junction Temperature

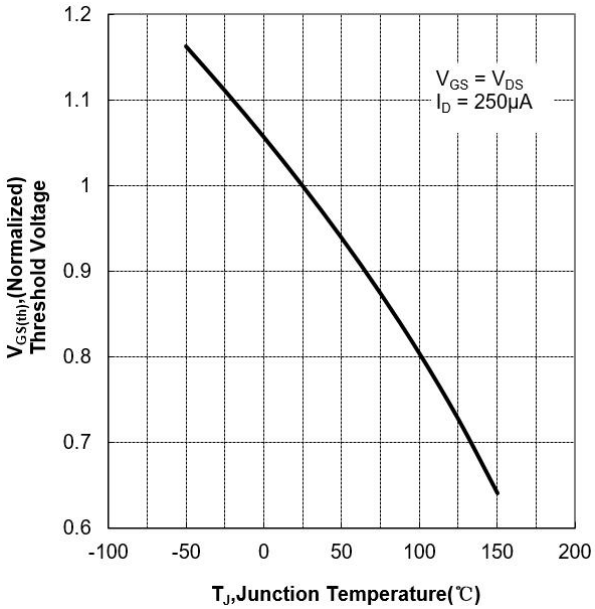


Figure 9 Typical Breakdown Voltage vs Junction Temperature

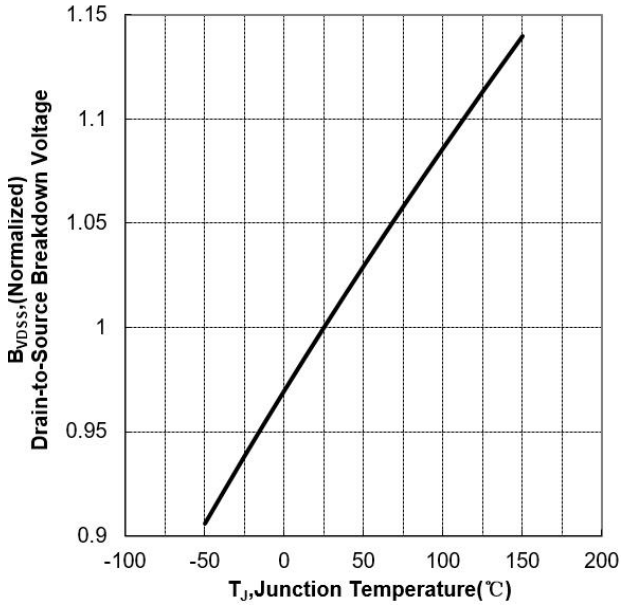
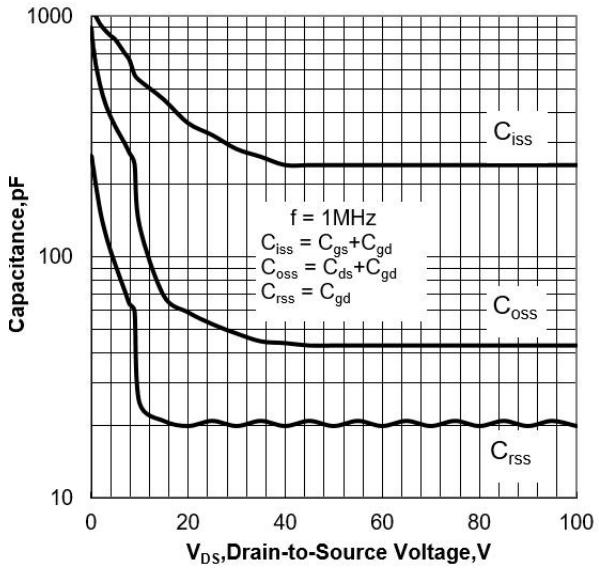
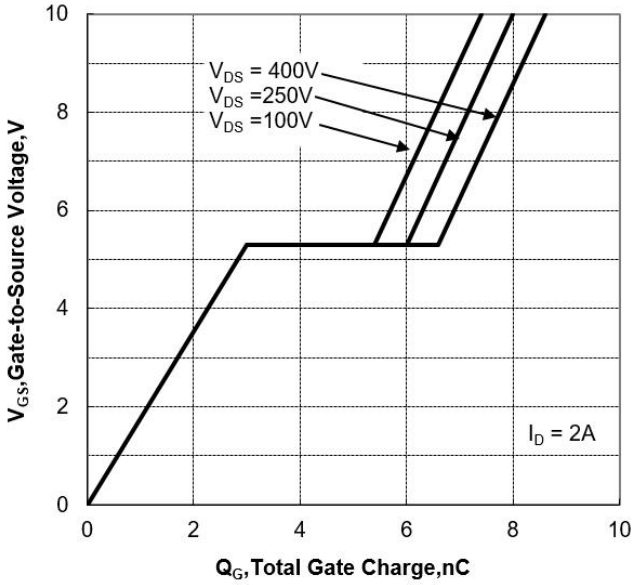


Figure 10 Typical Capacitance vs Drain to Source Voltage	Figure 11 Typical Gate Charge vs Gate to Source Voltage





Test Circuit and Waveform

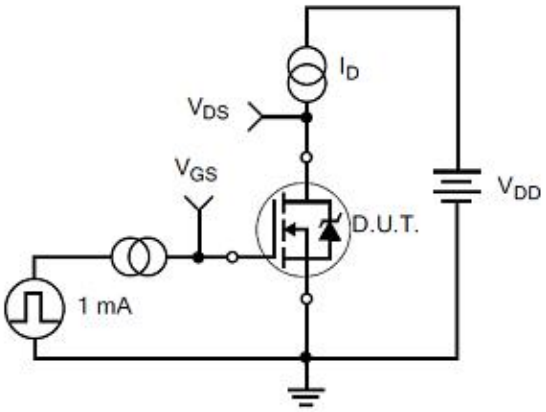
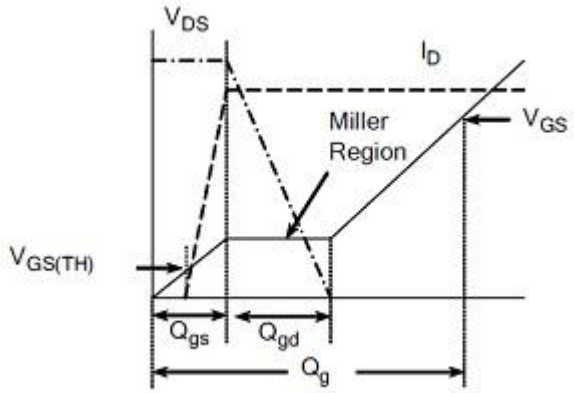
Figure 12 Gate Charge Test Circuit	Figure 13 Gate Charge Waveforms
	

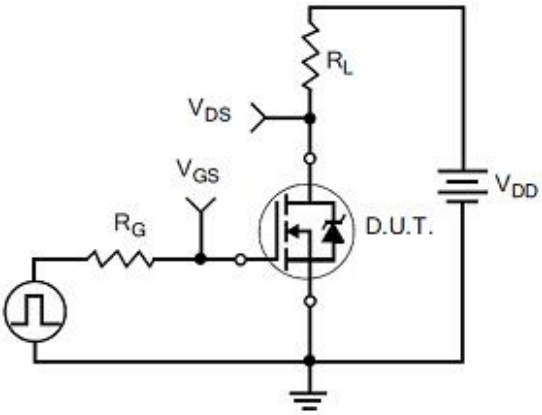
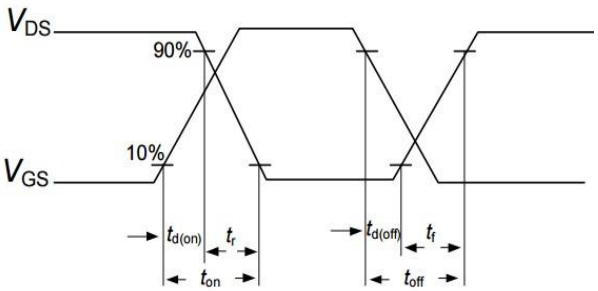
Figure 14 Resistive Switching Test Circuit	Figure 15 Resistive Switching Waveforms
	

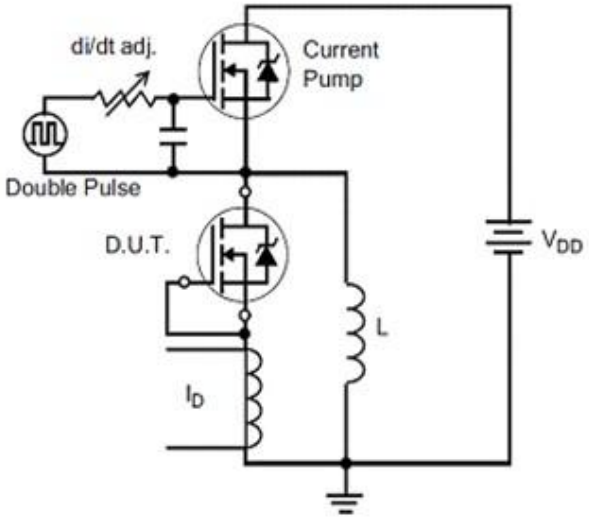
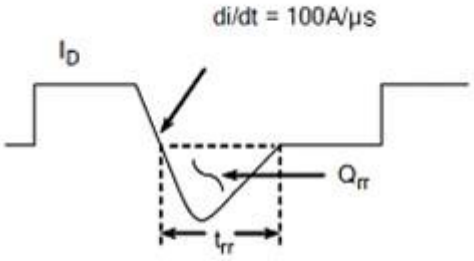
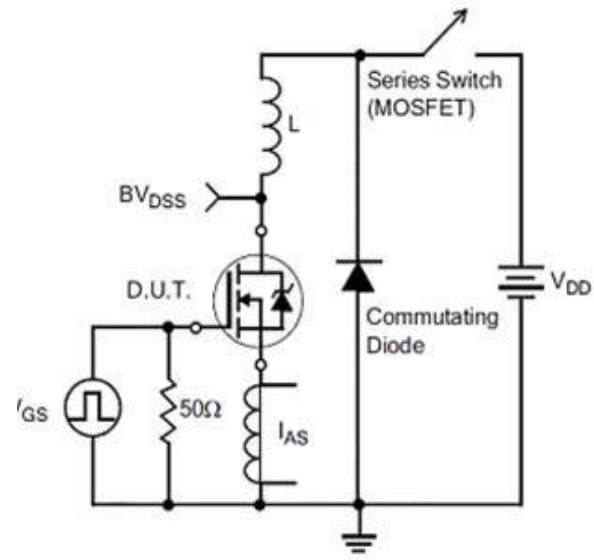
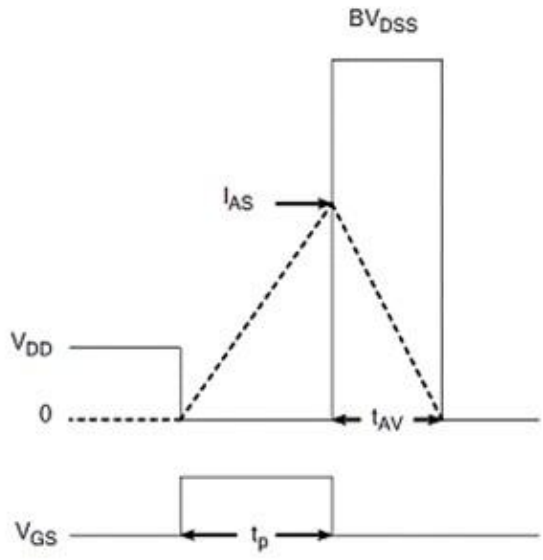
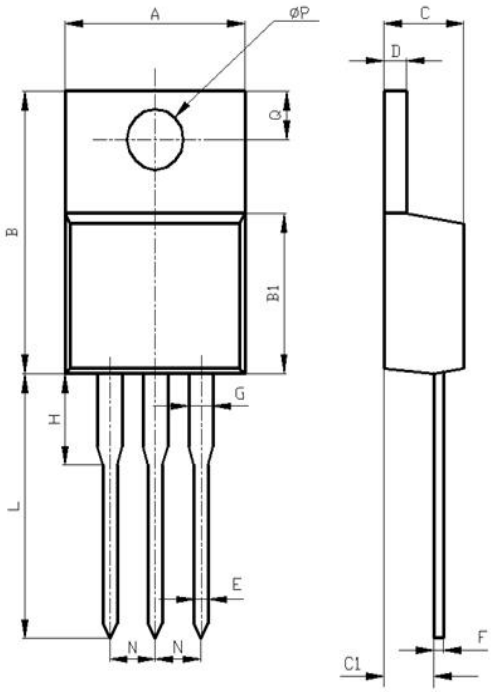
Figure 16 Diode Reverse Recovery Test Circuit	Figure 17 Diode Reverse Recovery Waveform
	

Figure 18 Unclamped Inductive Switching Test Circuit	Figure 19 Unclamped Inductive Switching Waveform
	

Package Description



Symbol	Values(mm)	
	MIN	MAX
A	9.60	10.6
B	15.0	16.0
B1	8.90	9.50
C	4.30	4.80
C1	2.30	3.10
D	1.20	1.40
E	0.70	0.90
F	0.30	0.60
G	1.17	1.37
H	2.70	3.80
L	12.6	14.8
N	2.34	2.74
Q	2.40	3.00
ΦP	3.50	3.90

TO-220 Package

NOTE:

1. Exceeding the maximum ratings of the device in performance may cause damage to the device, even the permanent failure, which may affect the dependability of the machine. Please do not exceed the absolute maximum ratings of the device when circuit designing.
2. When installing the heat sink, please pay attention to the torsional moment and the smoothness of the heat sink.
3. MOSFETs is the device which is sensitive to the static electricity, it is necessary to protect the device from being damaged by the static electricity when using it.
4. Shenzhen Minos reserves the right to make changes in this specification sheet and is subject to change without prior notice.

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